

IMPROVED THERMAL MANAGEMENT IN EV POWER ELECTRONICS WITH BORON NITRIDE FILLED POTTING COMPOUNDS

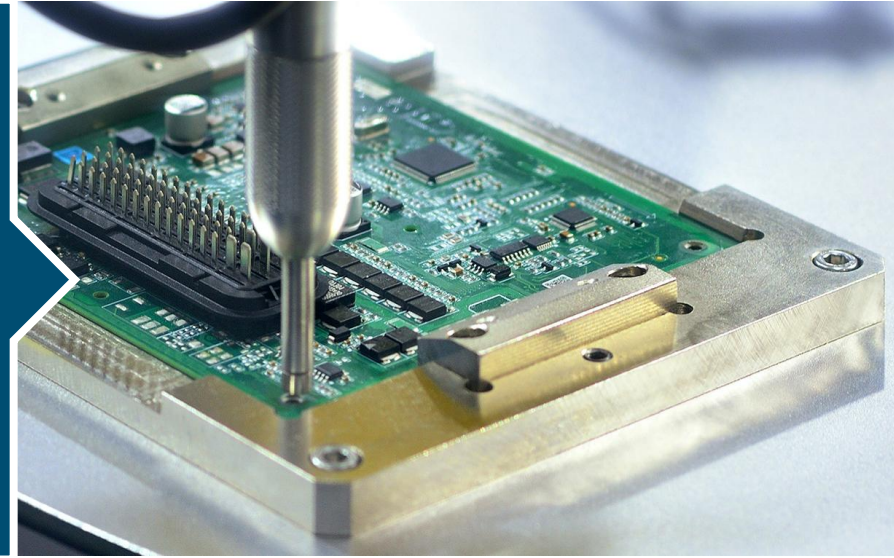
Anand Murugaiah, Ismail Nas, Bei Xiang
03/04/2025
IMAPS DPC 2025, Phoenix, AZ



MOMENTIVE[®]
TECHNOLOGIES



ADVANCED MATERIALS EXPERTS



We are an **Advanced Material Company** engaged in the design and manufacture of ultra-high-performance **Quartz** and **Ceramic** products. Momentive Technologies enables high-quality processing and production in a wide range of applications in the semiconductor, aerospace, water purification, pharmaceutical, consumer electronic and telecommunication industries.

GLOBAL MANUFACTURING AND TECHNICAL SERVICE FOOTPRINT

WILLOUGHBY, OH

Quartz Rods & Tubes

RICHMOND HEIGHTS, OH

Quartz Ingots

Quartz R&D

STRONGSVILLE, OH

Corporate Headquarters

Ceramic Powders, Coatings
& Solids Ceramics R&D

NEWARK, OH

Quartz Rods, Tubes
& Ingots

GEESTHACHT, GERMANY

Quartz Crucibles & Plates

WUXI, CHINA

Quartz Tubes & Crucibles

KOBE, JAPAN

Heater Assembly
Design & Test

KOZUKI, JAPAN

CVD Ceramics

OGUNI, JAPAN

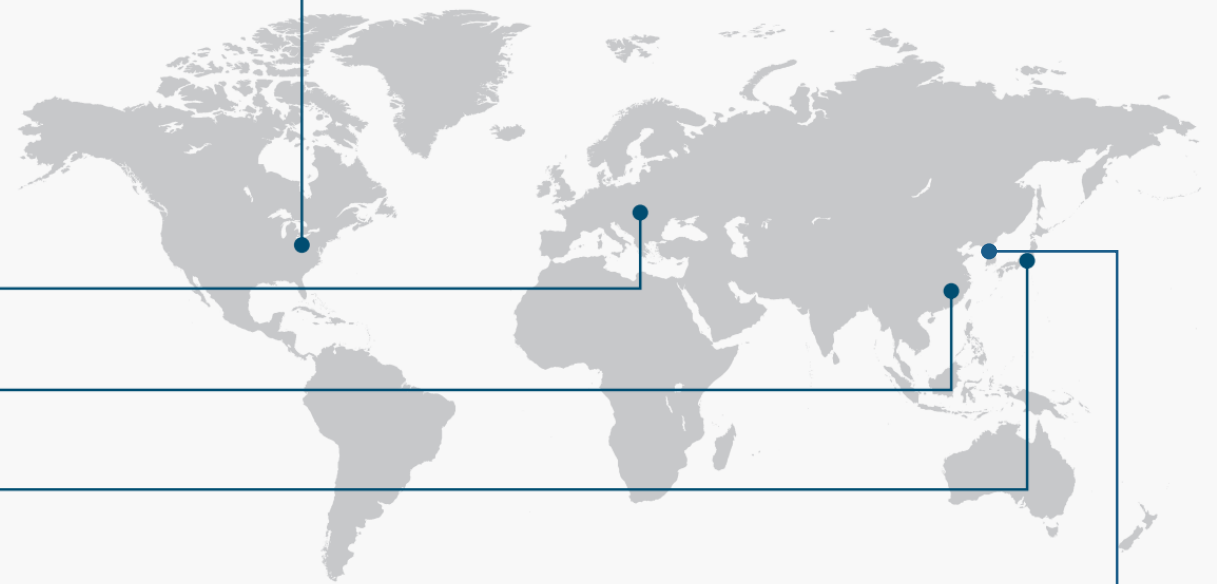
Quartz Crucibles

NAGASAKI, JAPAN

Purified Quartz Sand

SUNG DONG, REPUBLIC OF KOREA

Spherical Alumina & Spherical Silica Powders





CVD COATINGS

- **Tantalum Carbide**
- **Pyrolytic Boron Nitride**
- **Pyrolytic Graphite**



PRESSED & SINTERED SOLIDS

- **Hot-Pressed Boron Nitride Shapes**



POWDERS

- **Boron Nitride**
- **Boron Nitride-Based Paints**
- **Spherical Alumina**
- **Spherical Silica**
- **Titanium Diboride**

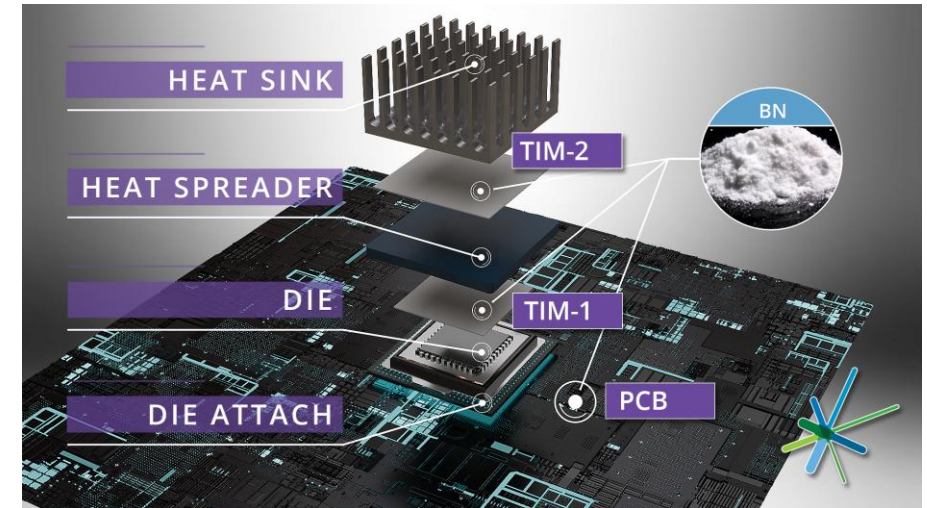


HEATERS & ELECTRO-STATIC CHUCKS

- **Pyrolytic Boron Nitride**
- **Assemblies**

HEXAGONAL BORON NITRIDE

- High Thermal Conductivity
- High Electrical Resistivity
- High Thermal Stability
- Low Dielectric Constant and Loss

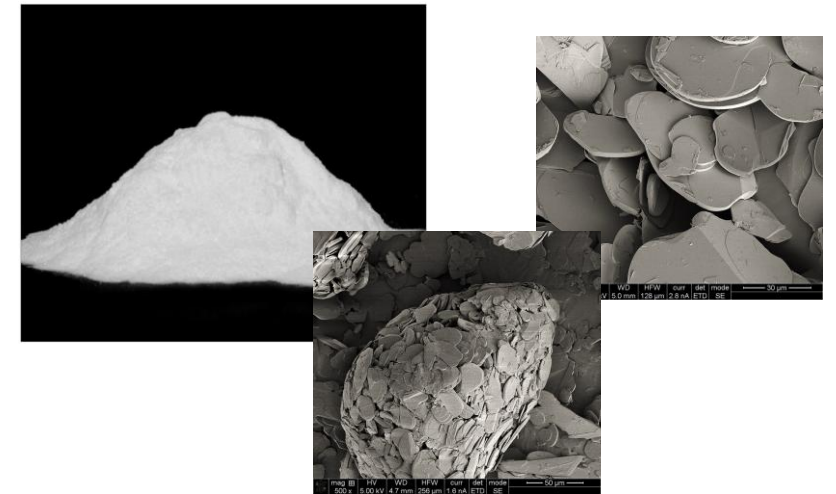
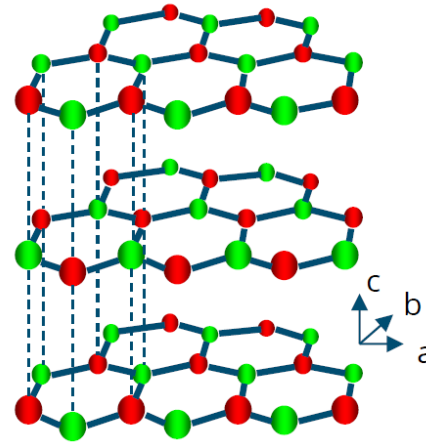


Typical Properties of Hexagonal Boron Nitride (h-BN)

Property	Typical value*
Theoretical Density	2.25 g/cc
Thermal Conductivity	300 W/mK [†]
Volume Resistivity	10 ¹⁵ Ohm-cm
Dielectric Constant	3.9
Mohs Hardness	1.5

*Typical properties are average data and are not to be used as, or to develop specifications

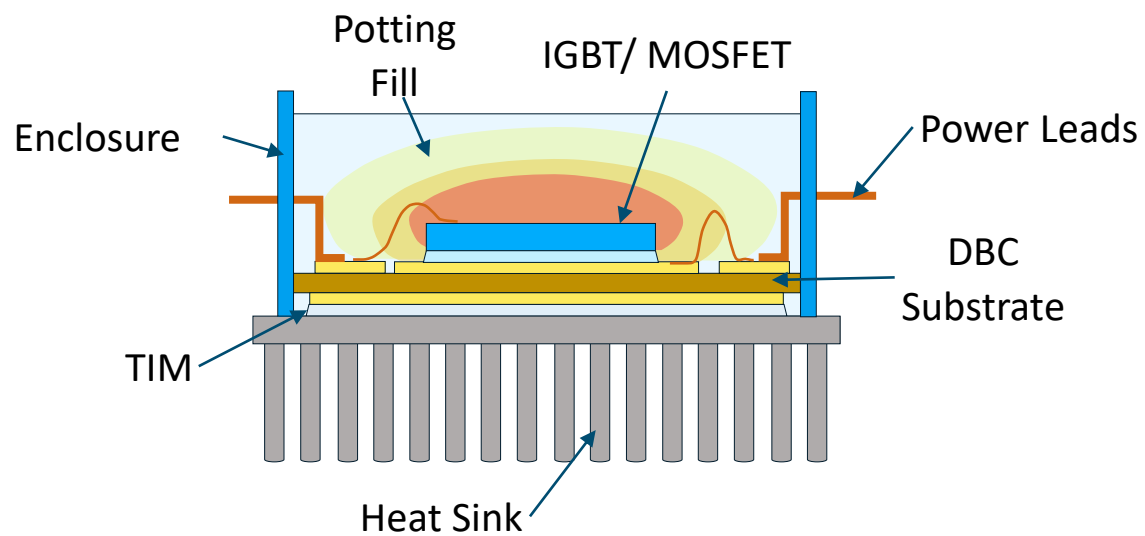
† In-plane conductivity in the a-b plane of the crystal



POWER MODULES AND THERMAL MANAGEMENT

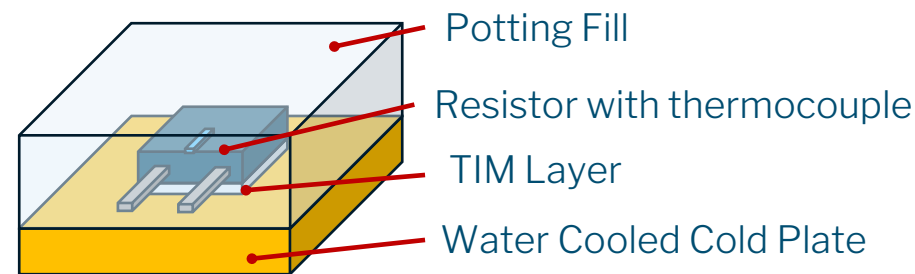
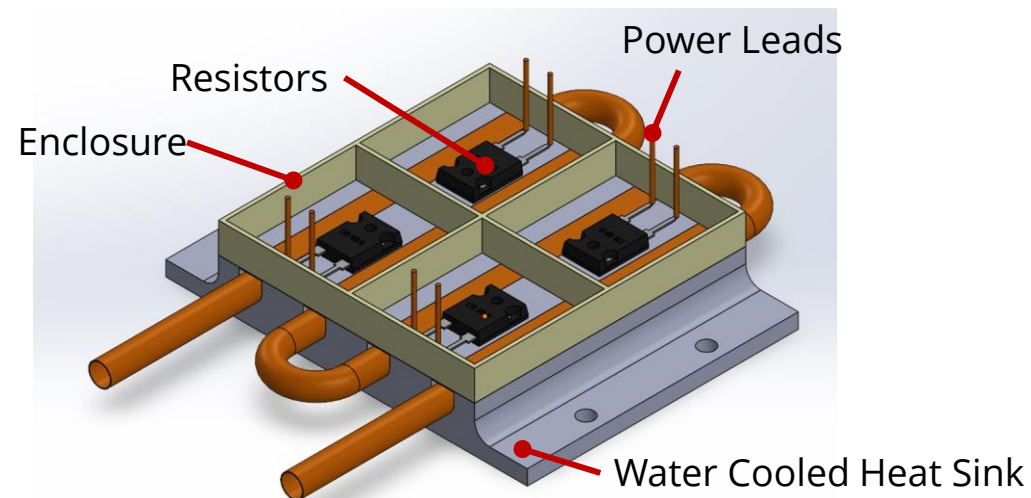
Most Power Modules (Half bridge/ full bridge, single side cooled devices):

- Heat Extraction from the bottom side (least thermal resistance)
- Top side potting generally with neat resin. So, not much top side heat removal.

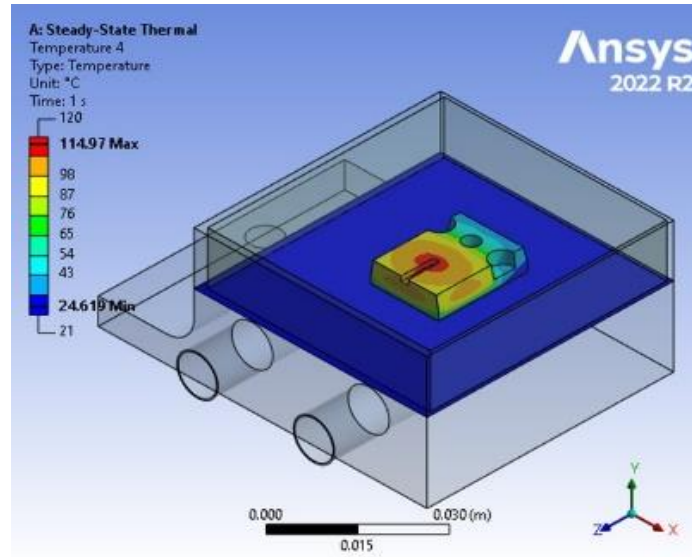
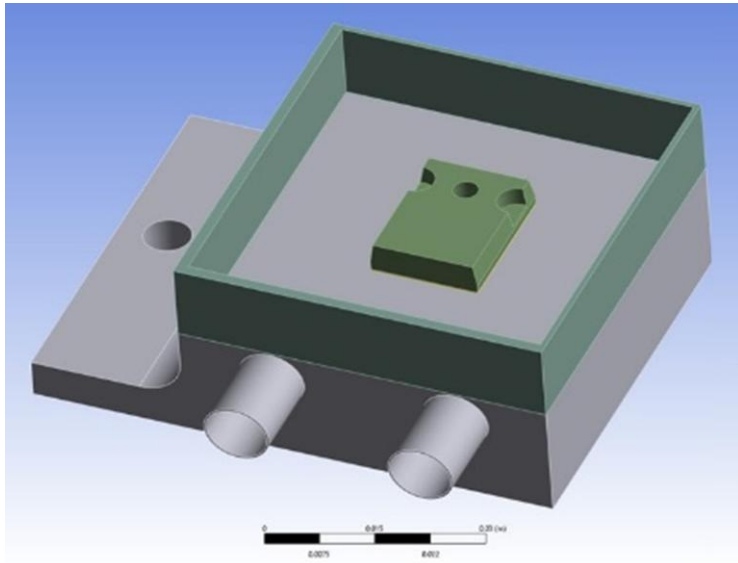


Simplified IGBT/ MOSFET cross section

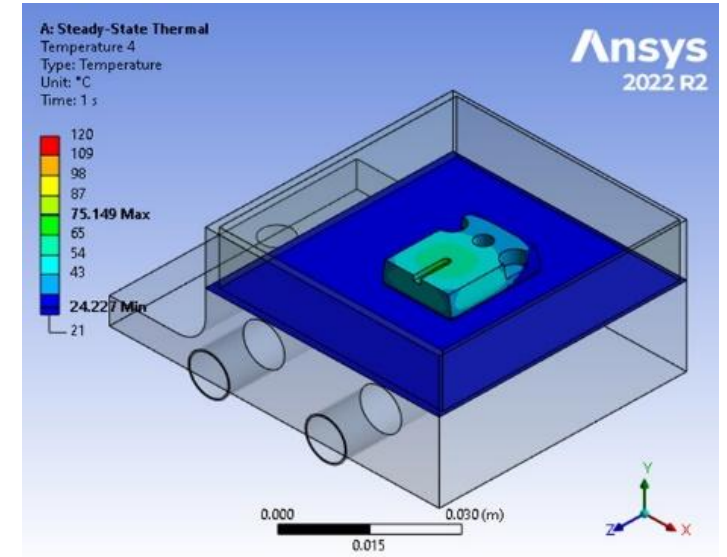
Demonstrator with resistors to Mimic IGBTs/MOSFETs



FINITE ELEMENT SIMULATIONS AND MODELING



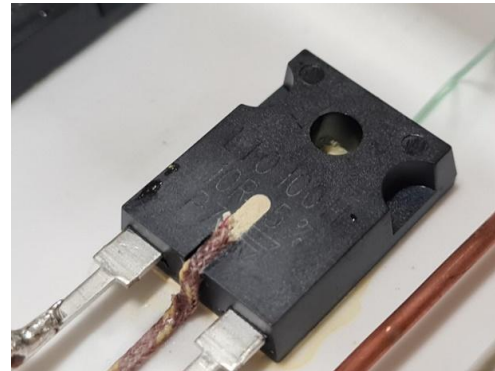
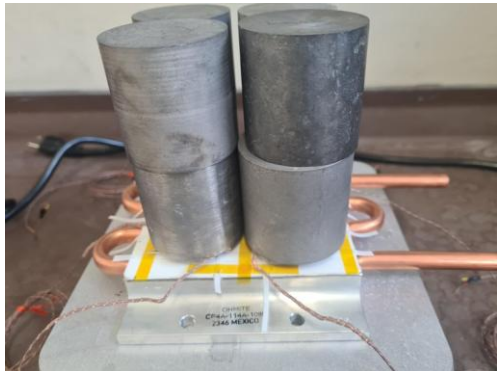
Pure Silicone Potting



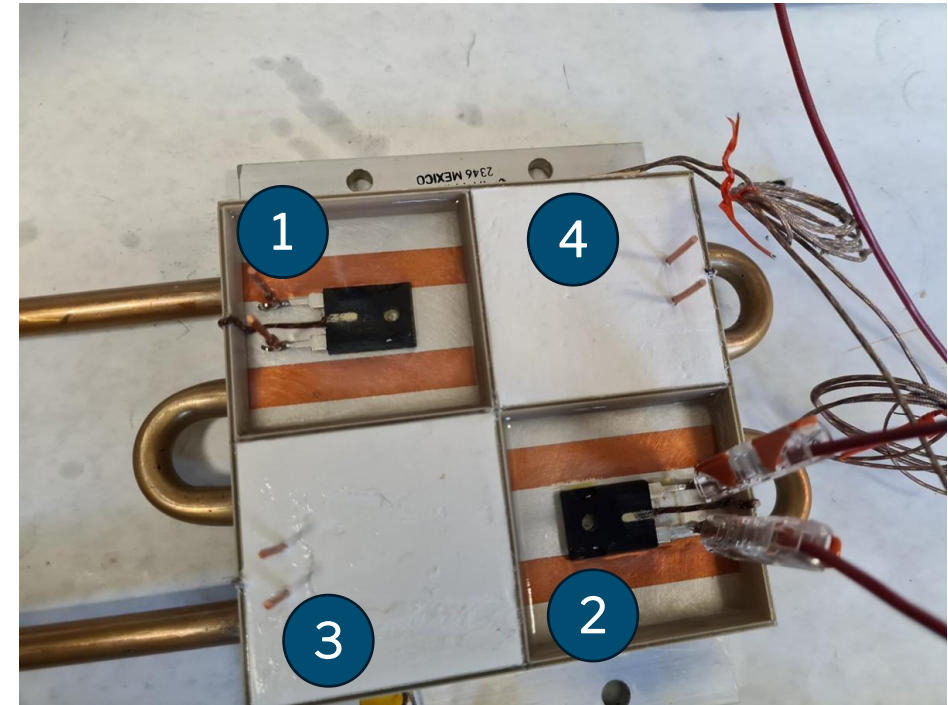
With BN Potting

- Boundary conditions were matched to experiment. Material properties as measured.
 - No additional assumptions or empirical corrections used
- a) Modeling $\frac{1}{4}$ of the device (one resistor) was sufficient
 - b) Temperature contour map of pure silicone potting at 100 Watts,
 - c) With BN Potting

DEMO MODULE CONSTRUCTION

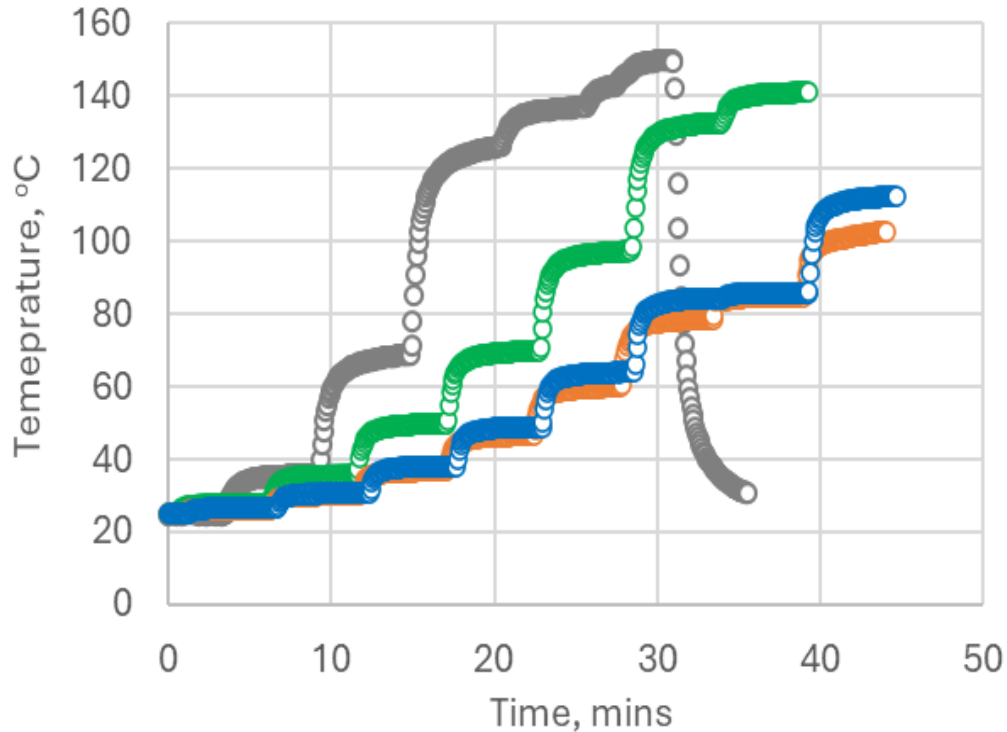


- **Case 1: Pure Resin in TIM and Potting (worst case)**
- **Case 2: BN TIM, Pure Resin Potting**
- **Case 3 & 4: BN TIM and BN Potting**

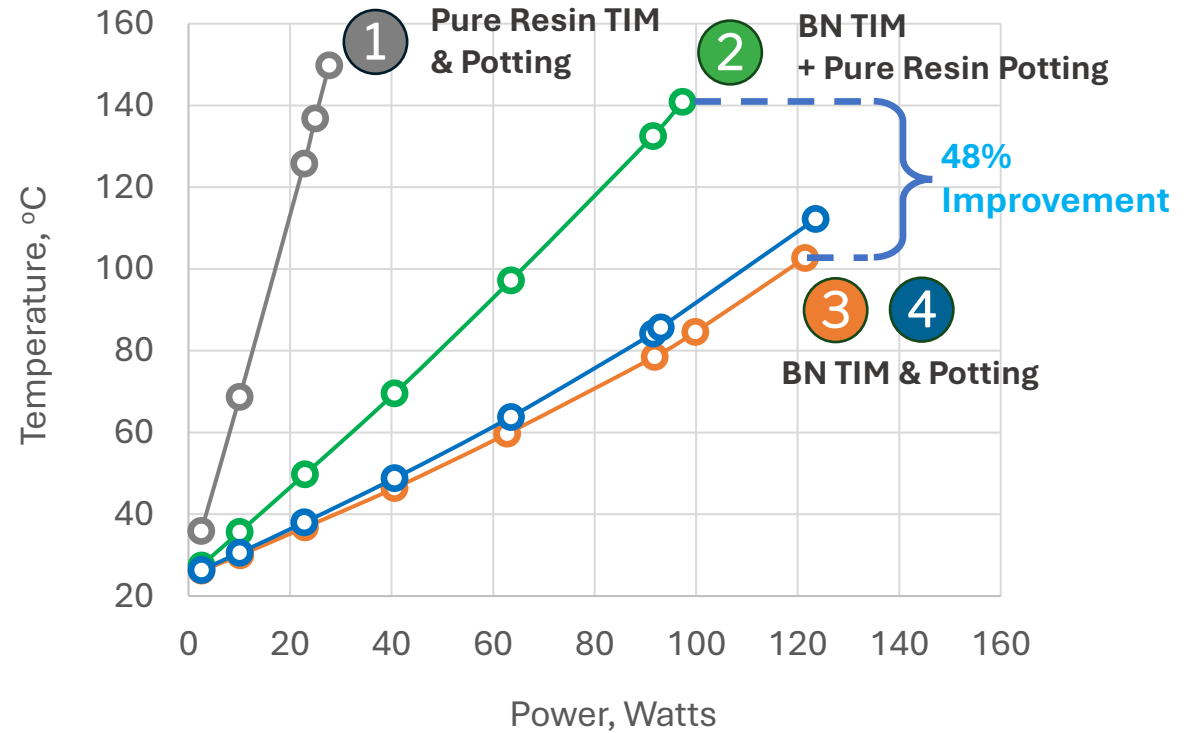


DEMO MODULE TESTING

Temperature vs. Time

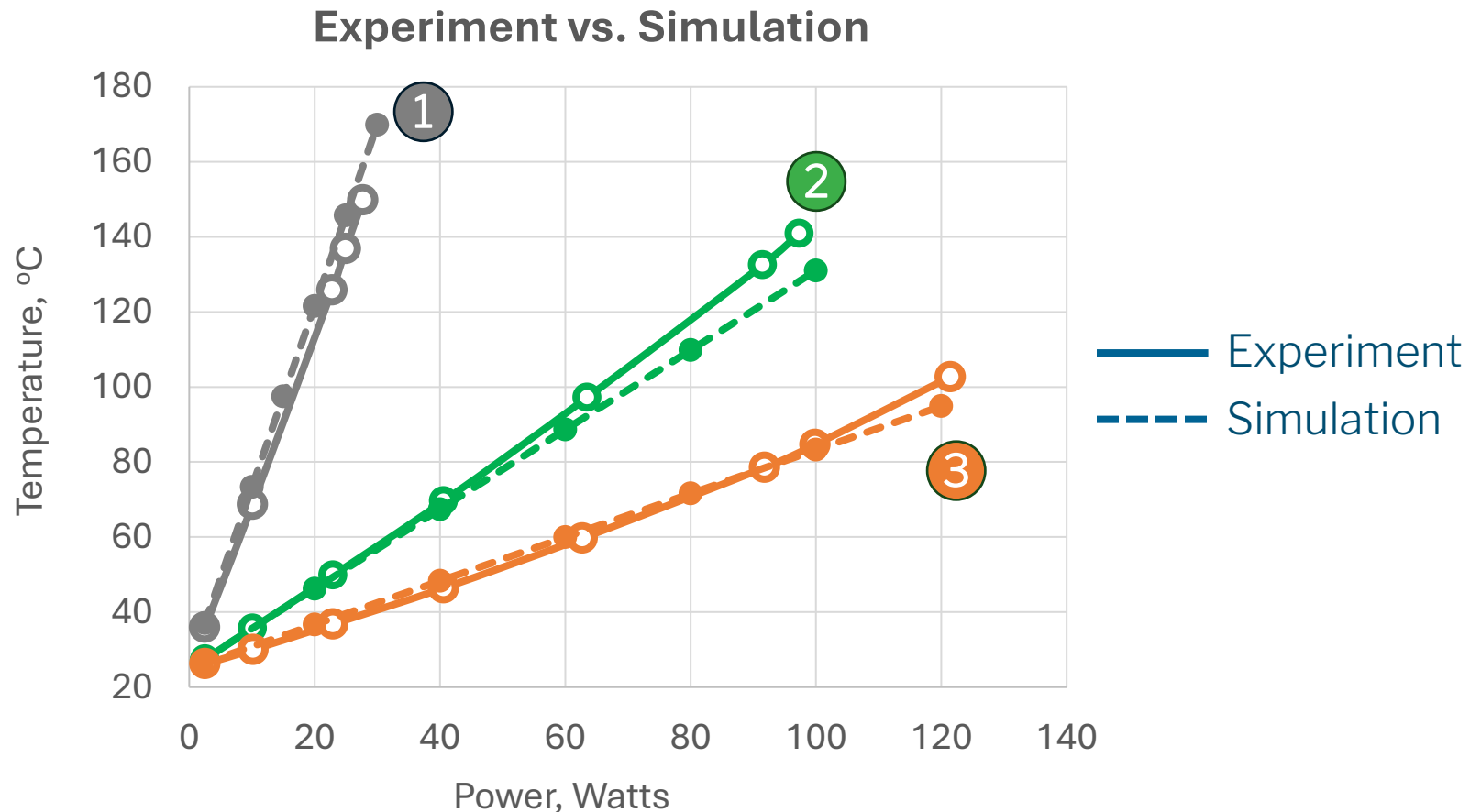


Temperature Response with Potting



- Resistors tested individually at various power settings till steady state
- Case 3 and 4 could be over driven to **~120%** of rated power due to improved thermal management

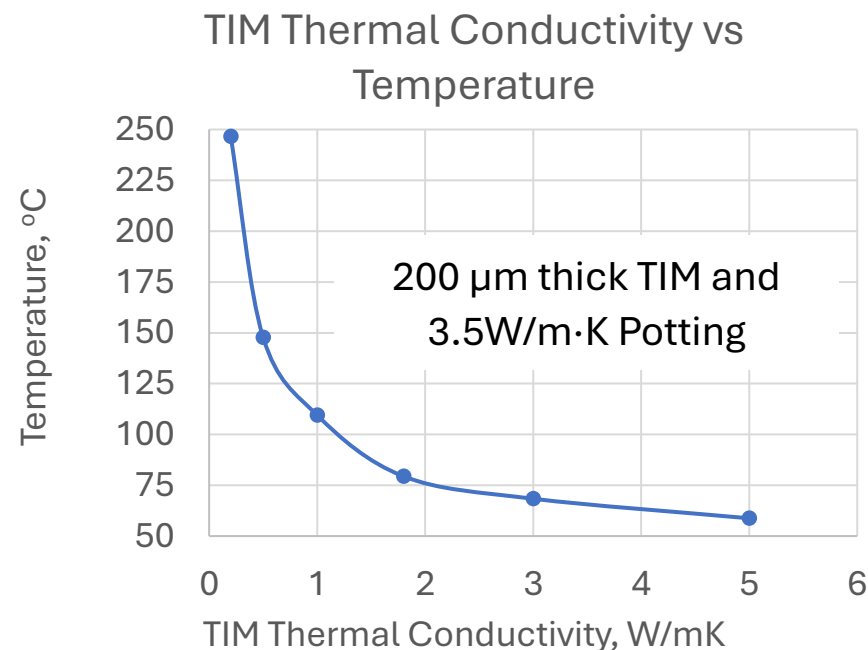
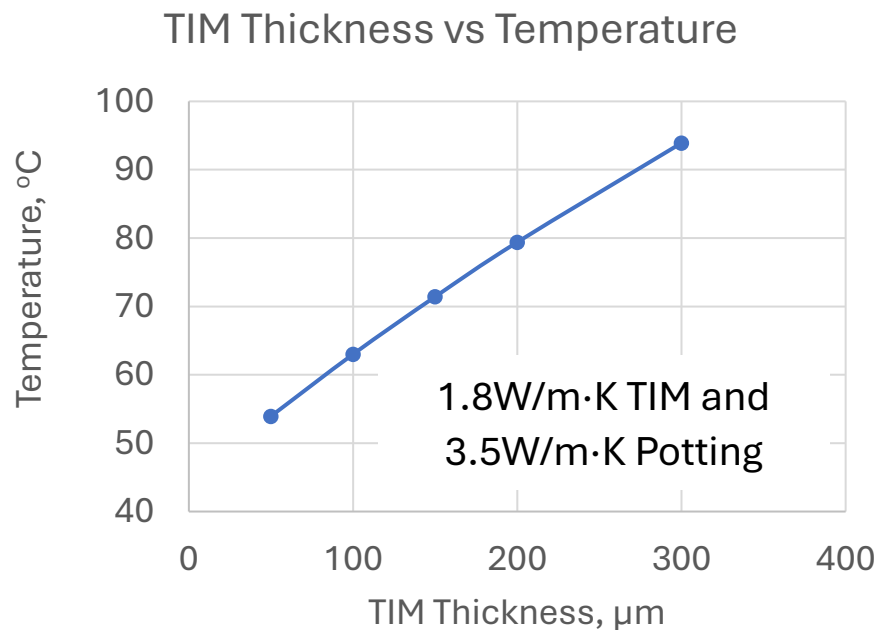
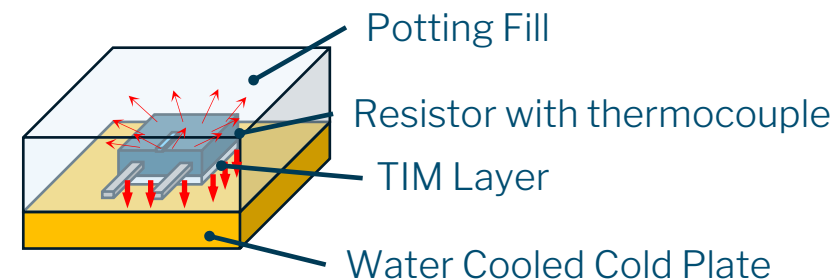
COMPARISON BETWEEN SIMULATION AND EXPERIMENT



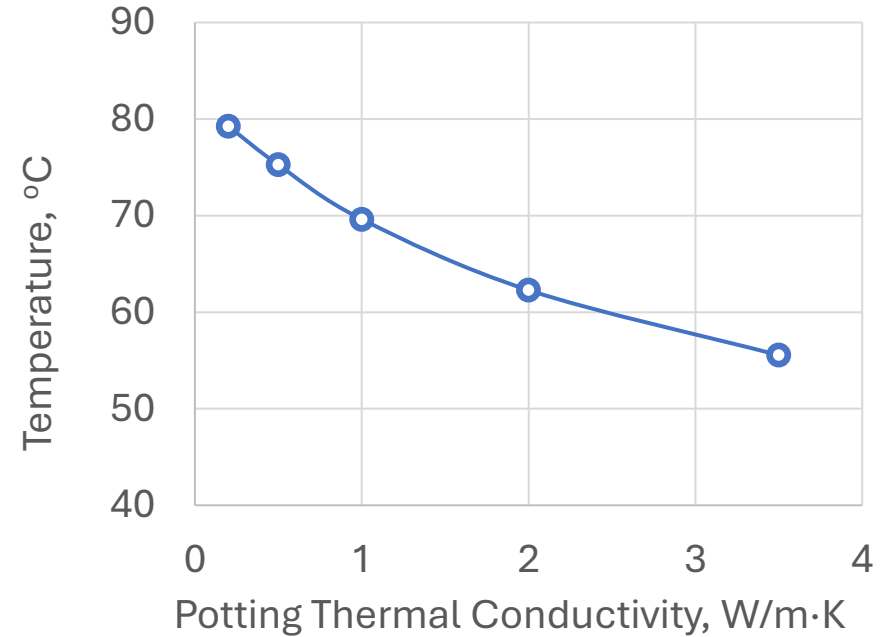
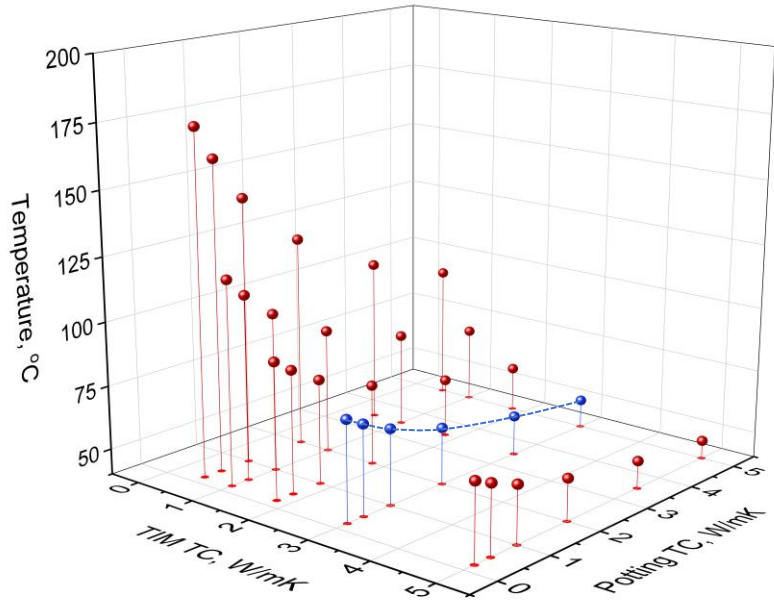
- Simulation showed excellent agreement with trials
- Significant hot spot temperature reduction at the chip
- Even with industry leading TIM at the bottom!

FACTORS AFFECTING HEAT DISSIPATION

- TIM Layer thickness and TIM thermal conductivity play a very important role



How much benefit will we get **despite** aggressive bottom side cooling?



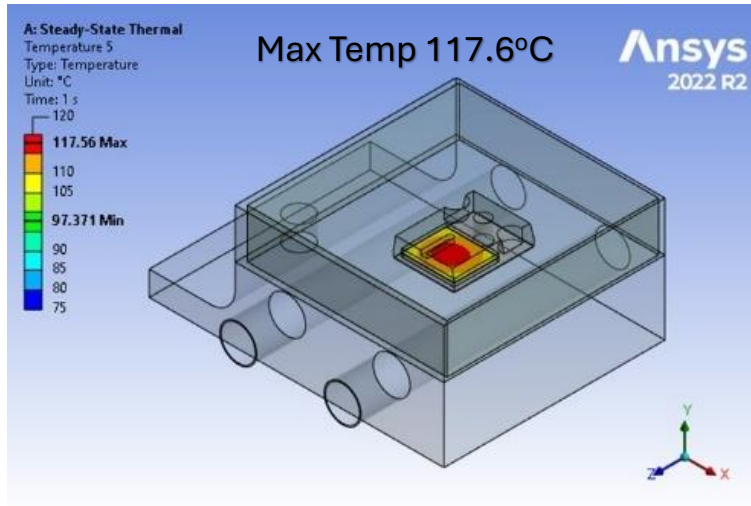
- **Significant reduction in resistor temperature even at premium TIM layer properties.**
- Blue pins in left has 3W/m·K TIM with 100 μ m thickness. Plotted separately on the right.

WHAT IF'S

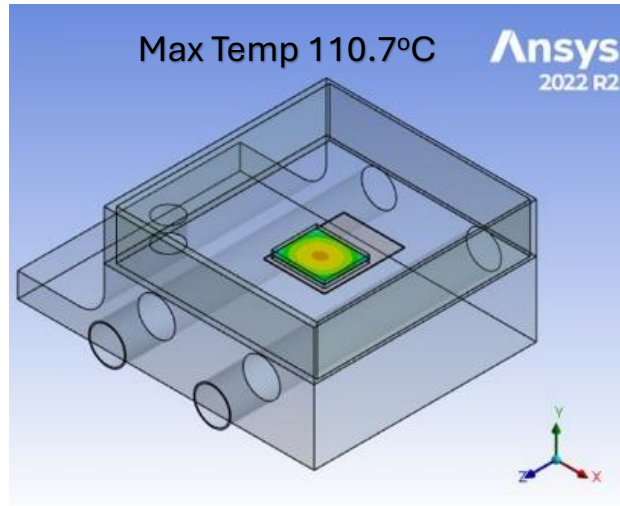
Effect of Epoxy Molding Compounds

Current Resistor $\sim 1 \text{ W/m}\cdot\text{k}$

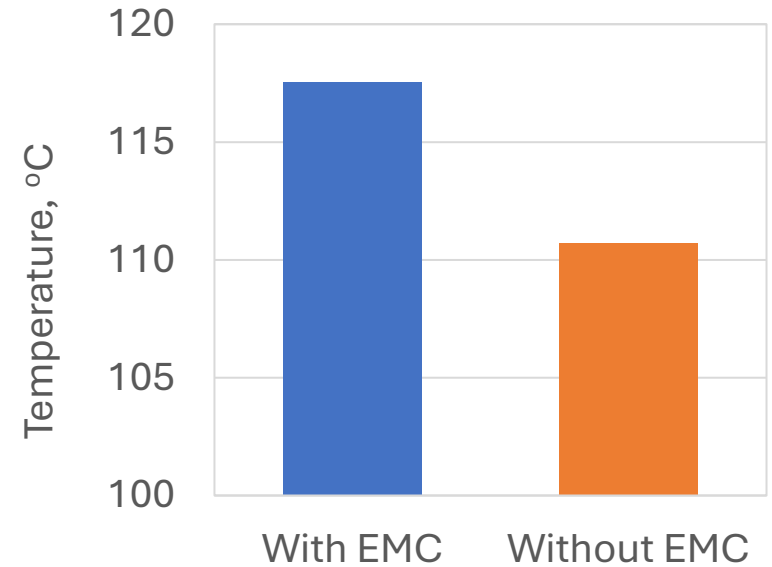
Actual MOSFETs can be up to $\sim 3 \text{ W/m}\cdot\text{k}$



With EMC



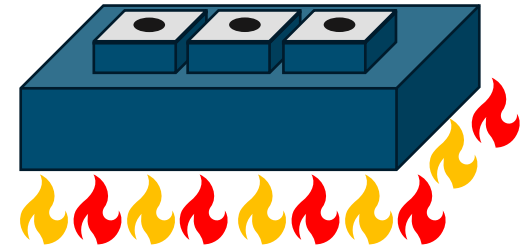
Without EMC



- Hottest temperature is at the resistor core
- If there were no EMC casing, the temperatures could be improved further

CONCLUSIONS

- Thermally conductive potting compounds such as BN fillers can significantly increase heat removal in power electronics
- Bottom side heat extraction may not be always sufficient in single sided power modules as demands increase
- Already critical thermal design in power electronics will further increase with expanded use
- BN's thermal conductivity, coupled with electrical insulation and low loss characteristics are attractive in high power, high frequency applications



THANK YOU

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